

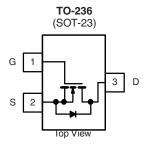
## SQ2325ES-T1-GE3-VB Datasheet N-Channel 200 V (D-S) MOSFET

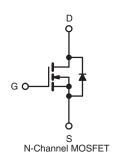
PRODUCT SUMMARY						
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)				
200	1.4 at V <sub>GS</sub> = 10 V	0.6				

#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- 100 % R<sub>g</sub> and UIS Tested
- Trench Power MOSFET
- Compliant to RoHS Directive 2002/95/EC







<b>ABSOLUTE MAXIMUM RATINGS</b>	6 (T <sub>A</sub> = 25 °C, unle	ess otherwise	noted)		_
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	200		V
Gate-Source Voltage		V <sub>GS</sub>	± 20		V
Continuous Dunin Comment /T 150 °C\ <sup>3</sup>	T <sub>A</sub> = 25 °C		0.6	0.45	Δ.
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C	- I <sub>D</sub>	0.5	0.35	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	2.5		Α
Avalanche Current <sup>b</sup>	L = 0.1 mH	I <sub>AS</sub>	2.5		
Single Avalanche Energy	L = 0.1 IIII	E <sub>AS</sub>	50		mJ
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	0.6		Α
Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	В	1.55 1.03		W
rower dissipation	T <sub>A</sub> = 70 °C	$P_{D}$	1.20	0.87	VV
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stq</sub>	- 55	to 150	°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 5 s	В	80	100		
Maximum Junction-to-Ambient	Steady State	R <sub>thJA</sub>	130	170	°C/W	
Maximum Junction-to-Foot	Steady State	R <sub>thJF</sub>	45	55		

### Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. Pulse width limited by maximum junction temperature.

服务热线:400-655-8788

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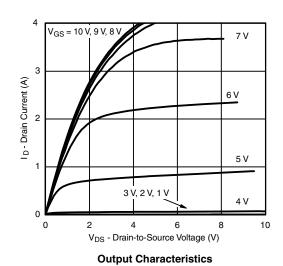
			Limits				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	$V_{DS}$	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 1 mA	200			V	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1.5		4.5	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zoro Coto Voltago Droin Current		$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ = 100 V, $V_{GS}$ = 0 V, $T_J$ = 70 °C			75	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 15 \text{ V}, V_{GS} = 10 \text{ V}$	2.5			Α	
Drain-Source On-Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.5 A		1.4		Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 0.5 A		4		S	
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> = 1 A, V <sub>GS</sub> = 0 V		0.8	1.2	V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_g$			3	5		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 100 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 0.5 \text{ A}$		0.37		nC	
Gate-Drain Charge	Q <sub>gd</sub>			1.45			
Gate Resistance	$R_g$		0.5	1.3	2.4	Ω	
Switching							
Turn-On Delay Time	t <sub>d(on)</sub>			7	11		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 100 V, $R_L$ = 33 $\Omega$		10	15		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong 0.2 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 6 \Omega$		9	15	ns	
Fall Time	t <sub>f</sub>			11	15		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 0.5 A, dI/dt = 100 A/μs50100					

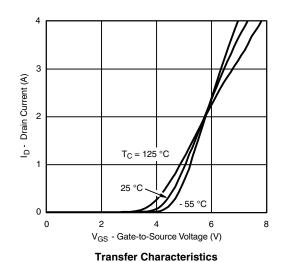
#### Notes:

- a. Pulse test: PW  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

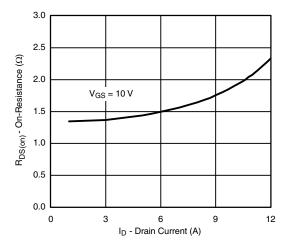
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



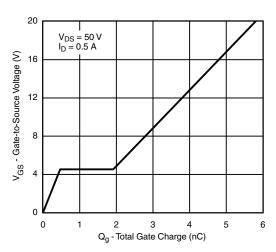




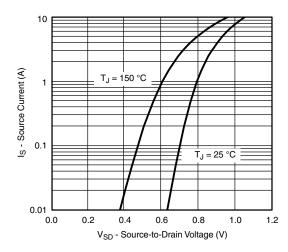
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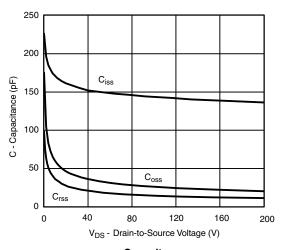
On-Resistance vs. Drain Current



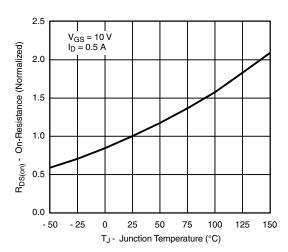
**Gate Charge** 



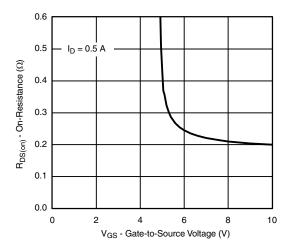
Source-Drain Diode Forward Voltage



Capacitance



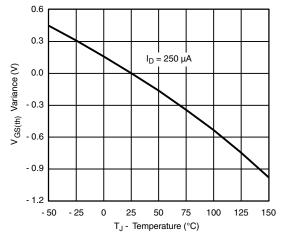
On-Resistance vs. Junction Temperature

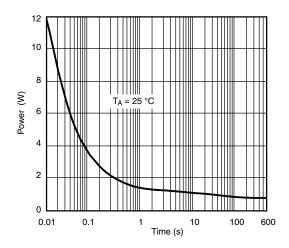


On-Resistance vs. Gate-to-Source Voltage



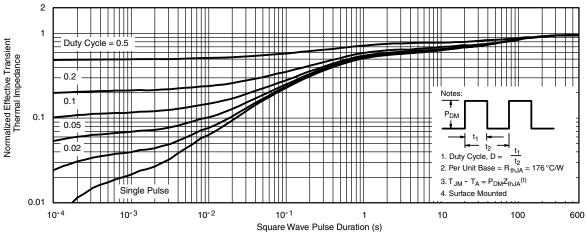
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





**Threshold Voltage** 

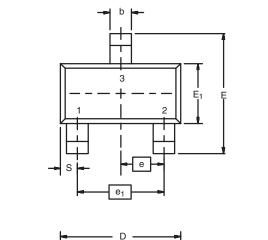
Single Pulse Power

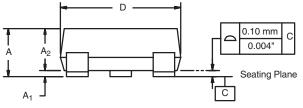


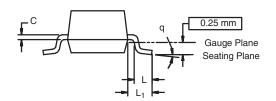
Normalized Thermal Transient Impedance, Junction-to-Ambient



### SOT-23 (TO-236): 3-LEAD







Dim	MILLIN	METERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A <sub>1</sub>	0.01	0.10	0.0004	0.004	
A <sub>2</sub>	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E <sub>1</sub>	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e <sub>1</sub>	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L <sub>1</sub>	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	

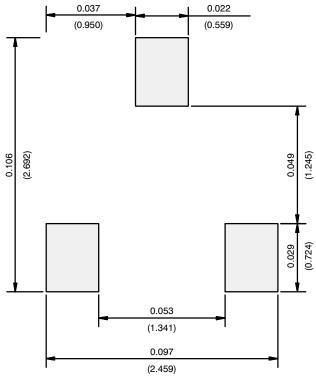
ECN: S-03946-Rev. K, 09-Jul-01

DWG: 5479



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#### **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)



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